

• General Description

The AGM314MAP combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$.

This device is ideal for load switch and battery protection applications.

• Features

- Advance high cell density Trench technology
- Low $R_{DS(ON)}$ to minimize conductive loss
- Low Gate Charge for fast switching
- Low Thermal resistance
- 100% Avalanche tested
- 100% DVDS tested

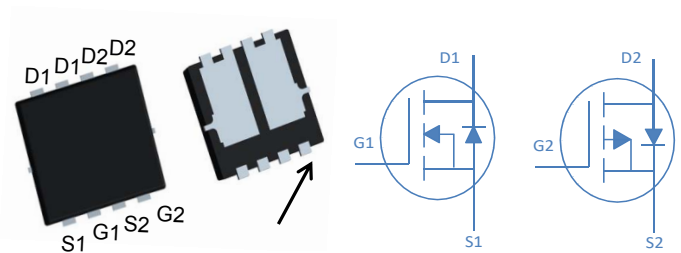
• Application

- MB/VGA Vcore
- SMPS 2nd Synchronous Rectifier
- POL application
- BLDC Motor driver

Product Summary

BVDSS	RDSON	ID
30V	9mΩ	30A
-30V	18.5mΩ	-20A

PDFN3.3*3.3 Pin Configuration



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
AGM314MAP	AGM314MAP	PDFN3.3*3.3	330mm	12mm	5000

Table 1. Absolute Maximum Ratings (TA=25°C)

Symbol	Parameter	Rating		Units
		N-Ch	P-Ch	
V_{DS}	Drain-Source Voltage ($V_{GS}=0V$)	30	-30	V
V_{GS}	Gate-Source Voltage ($V_{DS}=0V$)	±20	±20	V
I_D	Drain Current-Continuous($T_C=25^\circ C$) (Note 1)	30	-20	A
	Drain Current-Continuous($T_C=100^\circ C$)	21	-14	A
IDM (pluse)	Drain Current-Continuous@ Current-Pulsed (Note 2)	120	-80	A
P_D	Total Power Dissipation($T_C=25^\circ C$)	29.7	29.7	W
	Total Power Dissipation($T_C=100^\circ C$)	11.9	11.9	W
EAS	Avalanche energy (Note 3)	15	17	mJ
T_J, T_{STG}	Operating Junction and Storage Temperature Range	-55 To 150	-55 To 150	°C

Table 2. Thermal Characteristic

Symbol	Parameter	Typ	Max	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient (Steady State) ¹	---	70	°C/W
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	4.2	°C/W

Table 3. N- Channel Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
On/Off States						
BVDSS	Drain-Source Breakdown Voltage	VGS=0V ID=250μA	30	--	--	V
IDSS	Zero Gate Voltage Drain Current	VDS=30V, VGS=0V	--	--	1	μA
IGSS	Gate-Body Leakage Current	VGS=±20V, VDS=0V	--	--	±100	nA
VGS(th)	Gate Threshold Voltage	VDS=VGS, ID=250μA	1.2	1.5	2.5	V
gFS	Forward Transconductance	VDS=5V, ID=5A	--	6	--	S
RDS(on)	Drain-Source On-State Resistance	VGS=10V, ID=10A	--	9	13	mΩ
		VGS=4.5V, ID=5A	--	14.5	30	mΩ
Dynamic Characteristics						
Ciss	Input Capacitance	VDS=15V, VGS=0V, F=1MHZ	--	550	--	pF
Coss	Output Capacitance		--	62	--	pF
Crss	Reverse Transfer Capacitance		--	50	--	pF
Rg	Gate resistance	VGS=0V, VDS=0V, f=1.0MHz	--	4.3	--	Ω
Switching Times						
td(on)	Turn-on Delay Time	VDS=15V, VGS=10V, RGEN=6.8Ω, RL=3.5Ω	--	12	--	nS
tr	Turn-on Rise Time		--	25	--	nS
td(off)	Turn-Off Delay Time		--	38	--	nS
tf	Turn-Off Fall Time		--	16	--	nS
Qg	Total Gate Charge	VGS=10V, VDS=15V, ID=15A	--	11.7	--	nC
Qgs	Gate-Source Charge		--	3.8	--	nC
Qgd	Gate-Drain Charge		--	2.3	--	nC
Source-Drain Diode Characteristics						
ISD	Source-Drain Current(Body Diode)		--	--	30	A
VSD	Forward on Voltage	VGS=0V, IS=10A	--	--	1.2	V
trr	Reverse Recovery Time	IF=10A , dI/dt=100A/μs , TJ=25°C	--	17	--	ns
Qrr	Reverse Recovery Charge		--	31	--	nc

Notes 1.The maximum current rating is package limited.

Notes 2.Repetitive Rating: Pulse width limited by maximum junction temperature

Notes 3.EAS condition: T_J=25°C

Table 3. P-Channel Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
On/Off States						
BVDSS	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250μA	-30	--	--	V
IDSS	Zero Gate Voltage Drain Current	V _{DS} =-30V, V _{GS} =0V	--	--	-1	μA
IGSS	Gate-Body Leakage Current	V _{GS} =±20V, V _{DS} =0V	--	--	±100	nA
VGS(th)	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =-250μA	-1.2	-1.5	-2.5	V
gFS	Forward Transconductance	V _{DS} =-10V, I _D =-5A	--	8	--	S
RDS(on)	Drain-Source On-State Resistance	V _{GS} =-10V, I _D =-10A	--	18.5	23	mΩ
		V _{GS} =-4.5V, I _D =-5A	--	27	32	mΩ
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} =-15V, V _{GS} =0V, F=1MHZ	--	750	--	pF
C _{oss}	Output Capacitance		--	155	--	pF
C _{rss}	Reverse Transfer Capacitance		--	93	--	pF
R _g	Gate resistance	V _{GS} =0V, V _{DS} =0V, f=1.0MHz	--	4.5	--	Ω
Switching Times						
t _{d(on)}	Turn-on Delay Time	V _{GS} =-10V, V _{DS} =-15V, R _L =1Ω, R _{GEN} =3Ω	--	9	--	nS
t _r	Turn-on Rise Time		--	5	--	nS
t _{d(off)}	Turn-Off Delay Time		--	21	--	nS
t _f	Turn-Off Fall Time		--	3.3	--	nS
Q _g	Total Gate Charge	V _{GS} =-10V, V _{DS} =-25V, I _D =-5A	--	13.2	--	nC
Q _{gs}	Gate-Source Charge		--	26	--	nC
Q _{gd}	Gate-Drain Charge		--	3.3	--	nC
Source-Drain Diode Characteristics						
ISD	Source-Drain Current(Body Diode)		--	--	-20	A
VSD	Forward on Voltage	V _{GS} =0V, I _S =-10A	--	--	-1.2	V
t _{rr}	Reverse Recovery Time	I _F =-10A, dI/dt=100A/μs, T _J =25°C	--	13	--	ns
Q _{rr}	Reverse Recovery Charge		--	8.5	--	nc

Notes 1.The maximum current rating is package limited.

Notes 2.Repetitive Rating: Pulse width limited by maximum junction temperature Notes

3.EAS condition: T_J=25°C

N-Channel Electrical Characteristics Diagrames

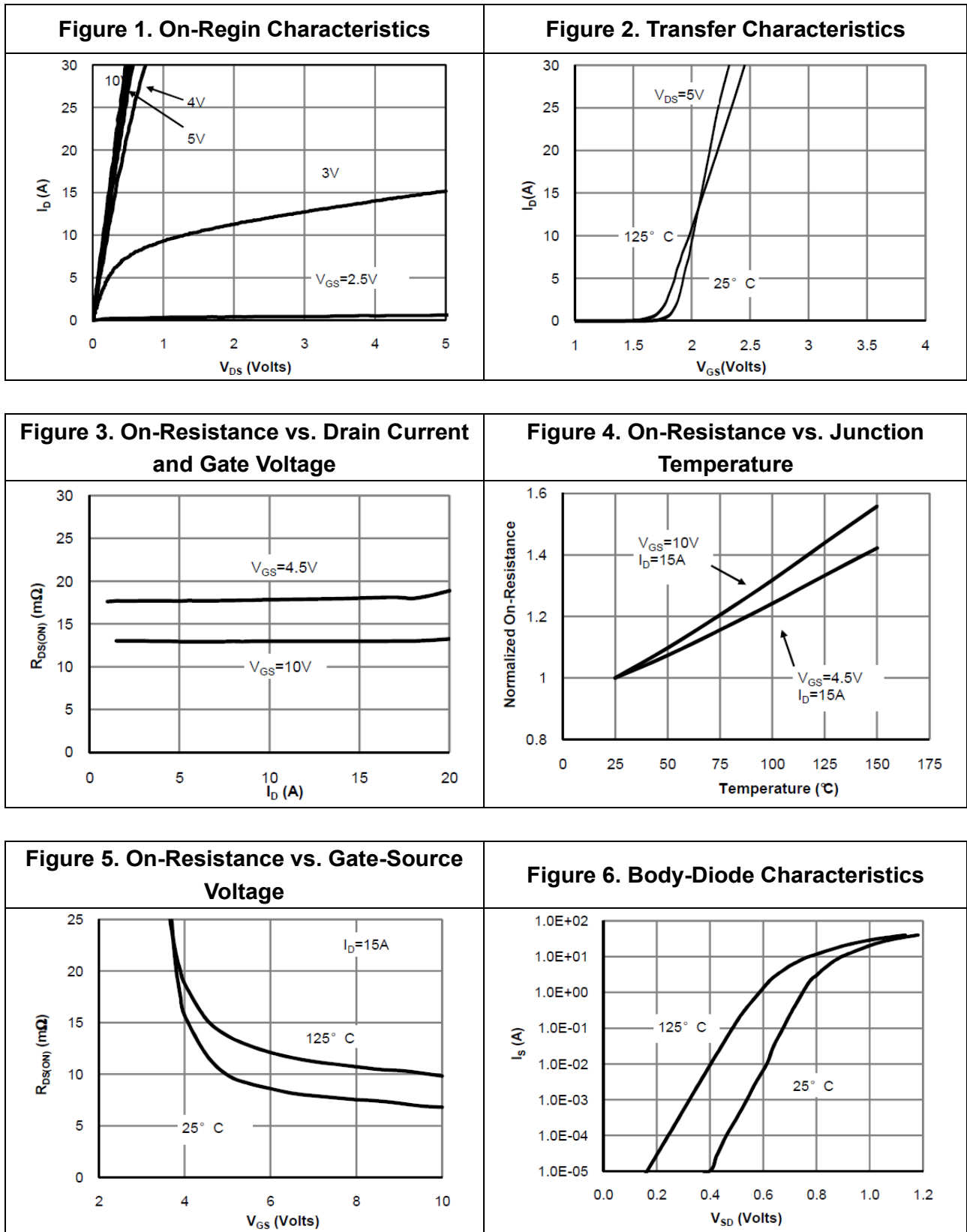


Figure 7. Gate-Charge Characteristics

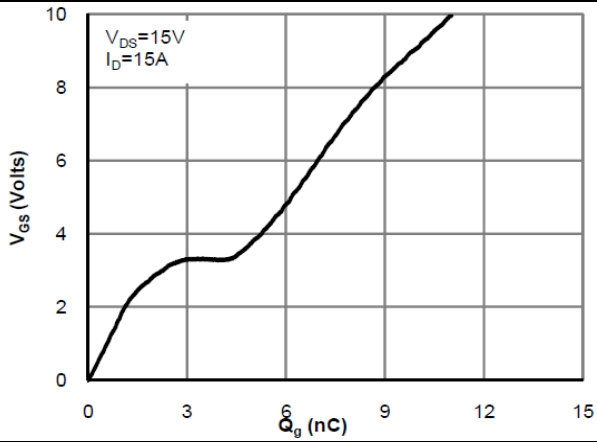


Figure 8. Capacitance Characteristics

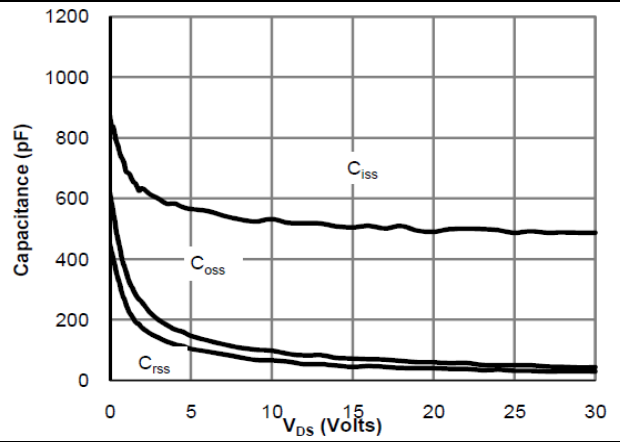


Figure 9. Maximum Forward Biased Safe Operating Area

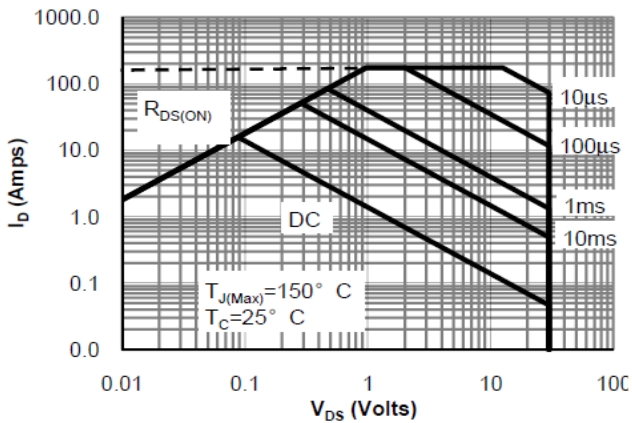


Figure 10. Single Pulse Power Rating Junction-to-Ambient

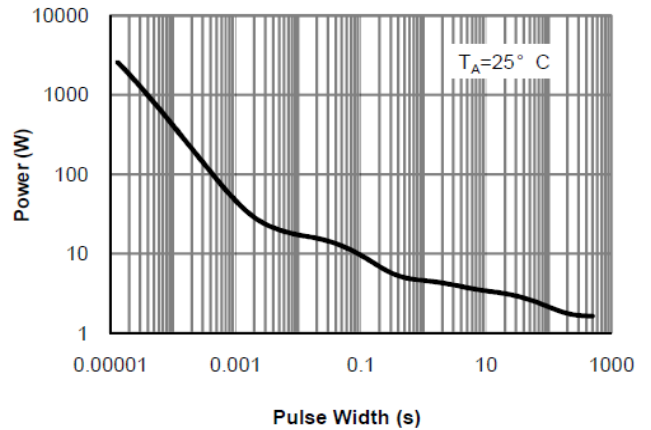
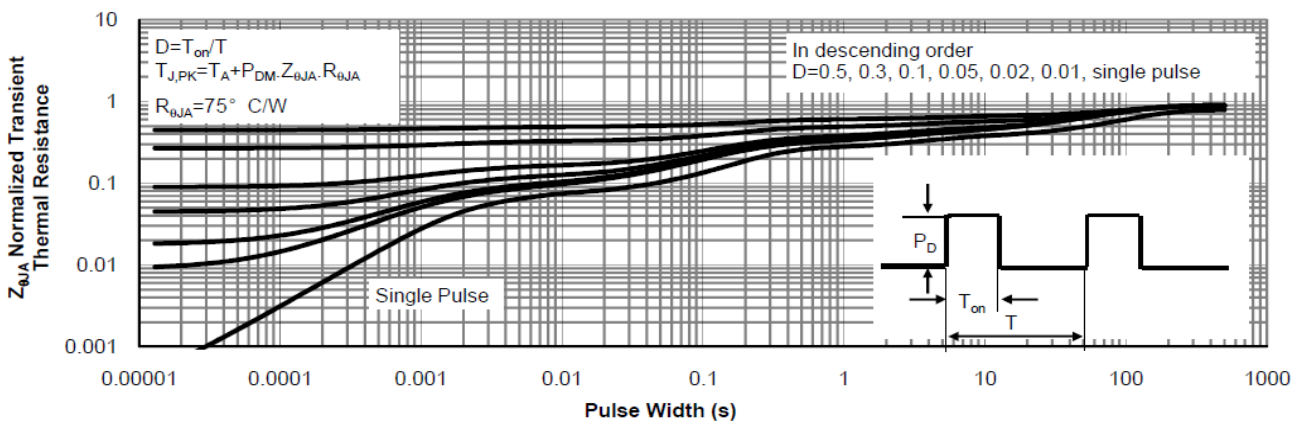


Figure 11. Normalized Maximum Transient Thermal Impedance



P-Channel Electrical Characteristics Diagrames

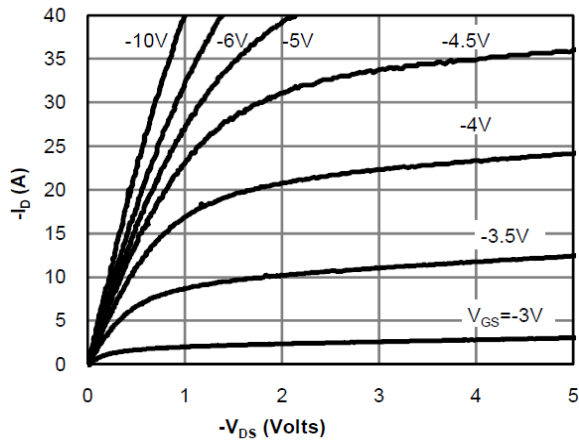
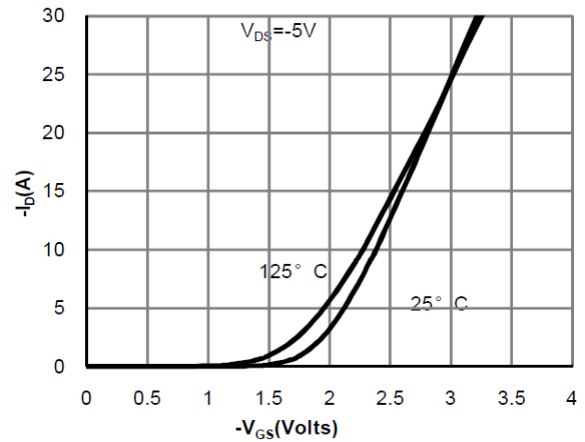
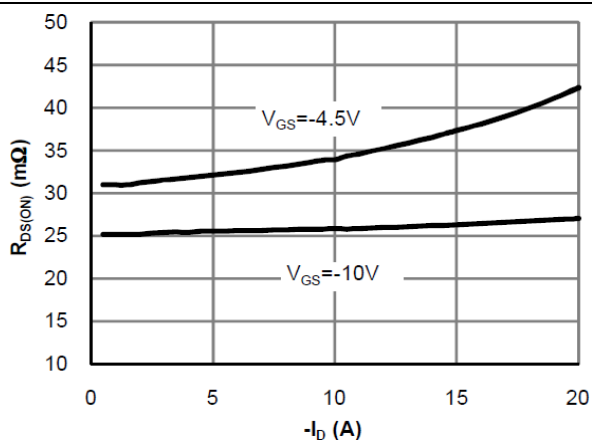
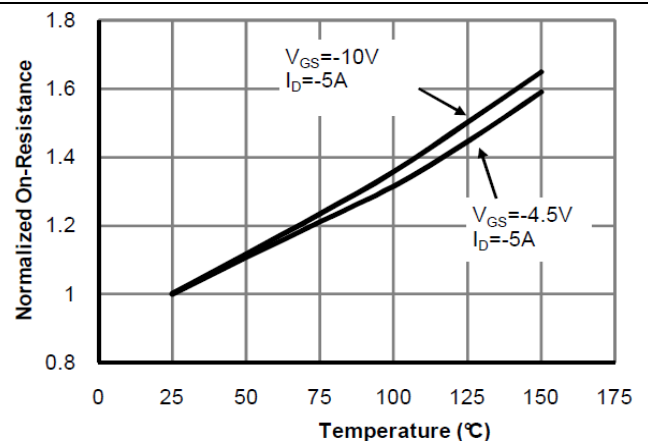
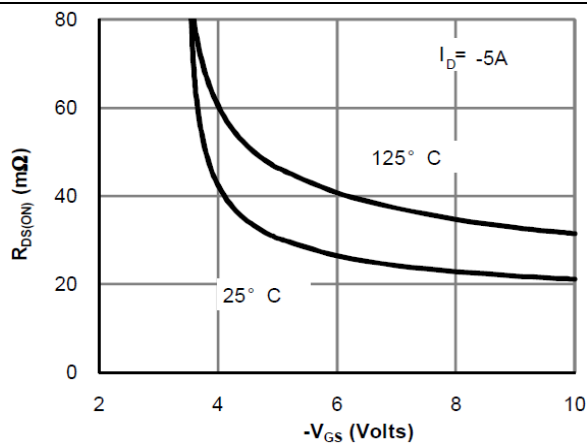
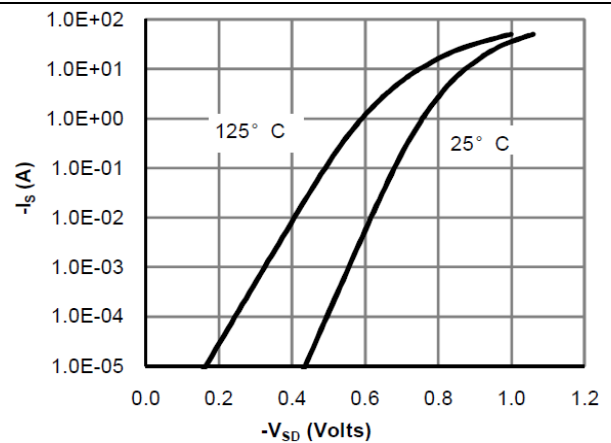
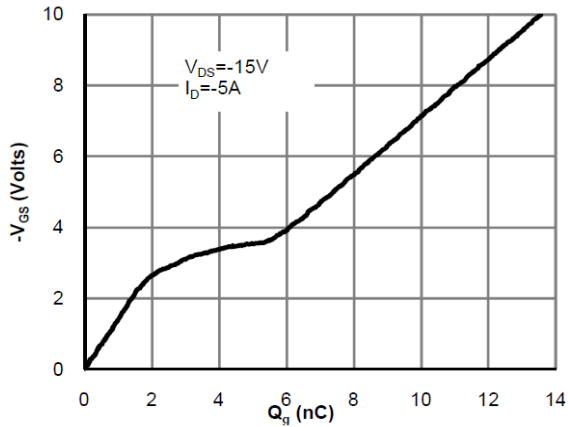
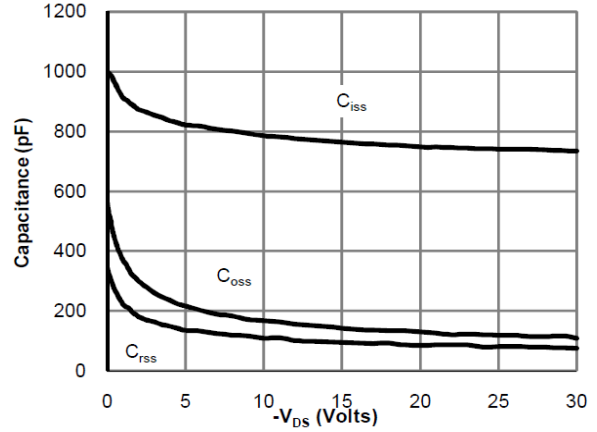
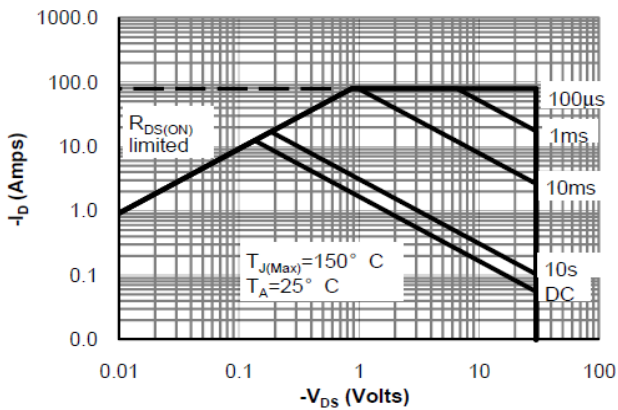
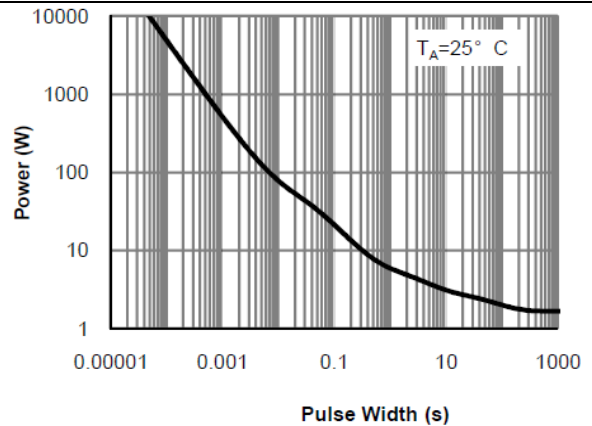
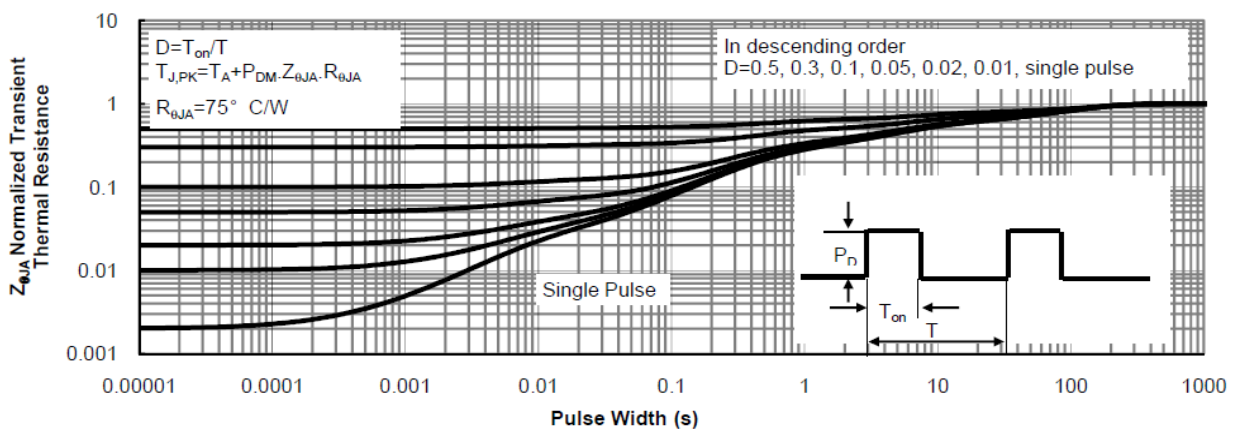
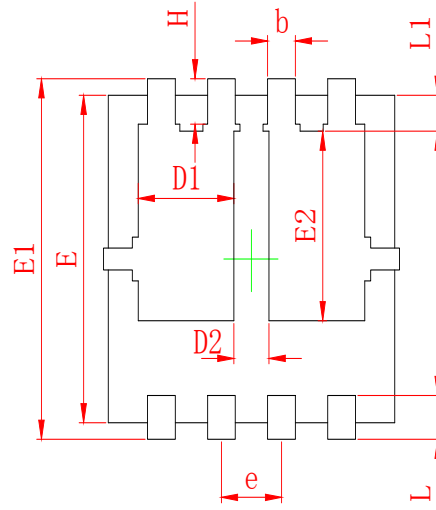
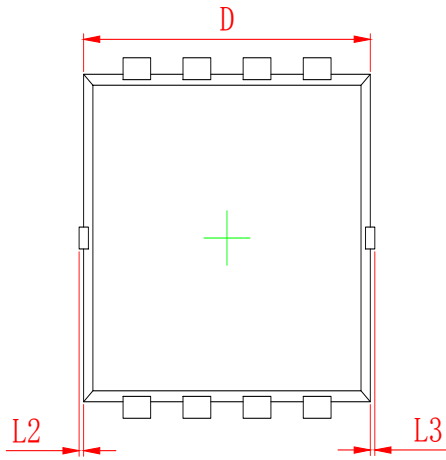
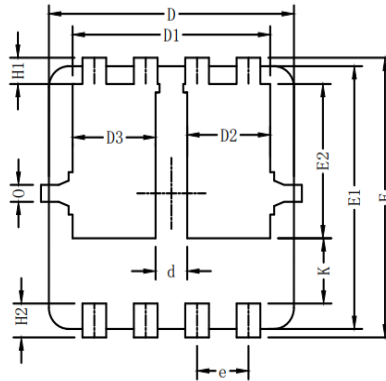
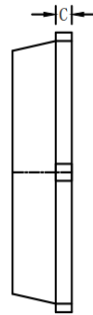
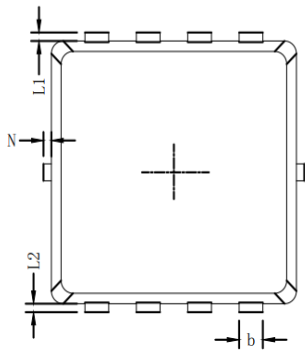
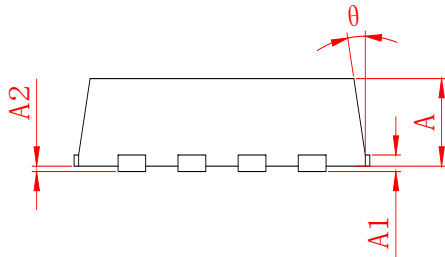
Figure 1. On-Regin Characteristics

Figure 2. Transfer Characteristics

Figure 3. On-Resistance vs. Drain Current and Gate Voltage

Figure 4. On-Resistance vs. Junction Temperature

Figure 5. On-Resistance vs. Gate-Source Voltage

Figure 6. Body-Diode Characteristics


Figure 7. Gate-Charge Characteristics

Figure 8. Capacitance Characteristics

Figure 9. Maximum Forward Biased Safe Operating Area

Figure 10. Single Pulse Power Rating Junction-to-Ambient

Figure 11. Normalized Maximum Transient Thermal Impedance


•Dimensions (PDFN3.3×3.3)


SYMBOL	MILLIMETER	
	MIN	MAX
A	0.700	0.900
A1	0.152 REF.	
A2	0°0.05	
D	3.000	3.200
D1	0.935	1.135
D2	0.280	0.480
E	2.900	3.100
E1	3.150	3.450
E2	1.535	1.935
b	0.200	0.400
e	0.550	0.750
L	0.300	0.500
L1	0.180	0.480
L2	0°0.100	
L3	0°0.100	
H	0.315	0.515
θ	8°	12°



Symbols	Millimeters		
	MIN.	NOM.	MAX.
A	0.65	0.75	0.85
b	0.25	0.30	0.35
C	0.15	0.20	0.25
D	3.00	3.10	3.20
D1	2.40	2.50	2.60
D2/D3	1.00	1.05	1.10
d	0.30	0.40	0.50
E	3.20	3.30	3.40
E1	3.00	3.10	3.20
E2	1.72	1.82	1.92
e	0.65 BSC.		
H1	0.21	0.31	0.41
H2	0.30	0.40	0.50
K	0.67	0.77	0.87
L1/L2	0.10 REF.		
θ	11°	12°	13°
N	0	-	0.15
0	0.2 REF.		


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